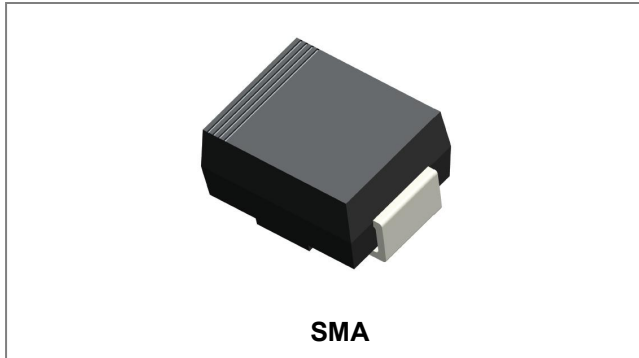


## SES1D SURFACE MOUNT SUPER FAST RECTIFIER



### Features

- Glass Passivated Die Construction
- Ideally Suited for Automatic Assembly
- Low Forward Overload Drop, High Efficiency
- Low Power Loss
- Super-Fast Recovery Time
- Plastic Case Material has UL Flammability Classification Rating 94V-O
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

### Circuit Diagram



### Mechanical Data

- Case: Low Profile Molded Plastic
- Terminals: Solder Plated, Solderable per MIL-STD-750, Method 2026
- Polarity: Cathode Band or Cathode Notch
- Weight: 0.06 grams(approx)

### Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	-	200	V
Average Rectified Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_L=110^\circ\text{C}$ , rectangular wave form	1	A
Peak One Cycle Non-Repetitive Surge Current	$I_{FSM}$	8.3ms, Half Sine pulse	30	A

### Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Forward Voltage Drop*	$V_{F1}$	@ 0.6A, Pulse, $T_J = 25^\circ\text{C}$ @ 1A, Pulse, $T_J = 25^\circ\text{C}$	0.865 0.92	V
Reverse Current*	$I_{R1}$	@ $V_R = \text{rated } V_R$ $T_J = 25^\circ\text{C}$	5	$\mu\text{A}$
	$I_{R2}$	@ $V_R = \text{rated } V_R$ $T_J = 125^\circ\text{C}$	100	$\mu\text{A}$
Junction Capacitance	$C_T$	@ $V_R = 5\text{V}$ , $T_C = 25^\circ\text{C}$ $f_{SIG} = 1\text{MHz}$	15	pF
Reverse Recovery Time	$t_{rr}$	$I_F=500\text{mA}$ , $I_R=1\text{A}$ , and $I_{rm}=250\text{mA}$	15	ns

\* Pulse width < 300  $\mu\text{s}$ , duty cycle < 2%

**Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	$T_J$	-	-55 to +150	$^{\circ}\text{C}$
Storage Temperature	$T_{stg}$	-	-55 to +150	$^{\circ}\text{C}$
Typical Thermal Resistance Junction to Ambient	$R_{\theta JA}$	DC operation	75	$^{\circ}\text{C}/\text{W}$
Approximate Weight	wt	-	0.09	g

**Ratings and Characteristics Curves**

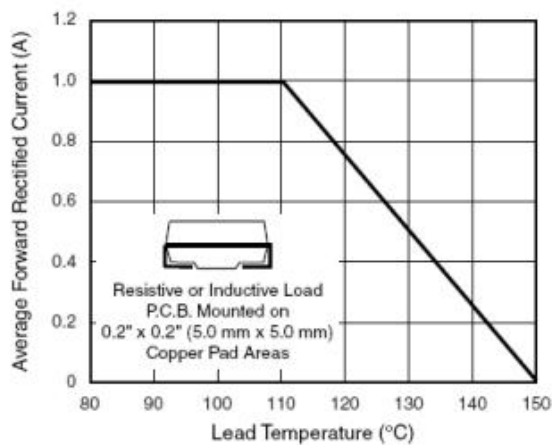


Fig. 1 - Maximum Forward Current Derating Curve

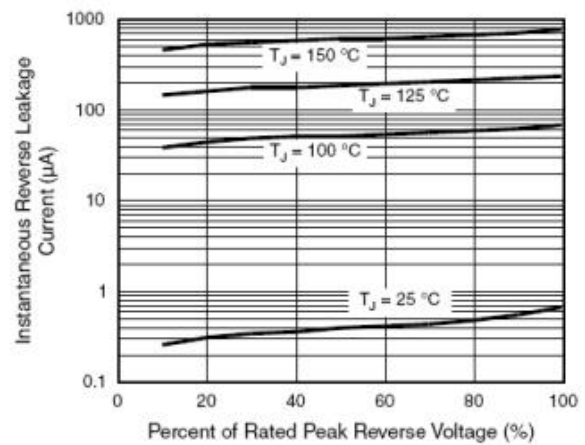


Fig. 4 - Typical Reverse Leakage Characteristics

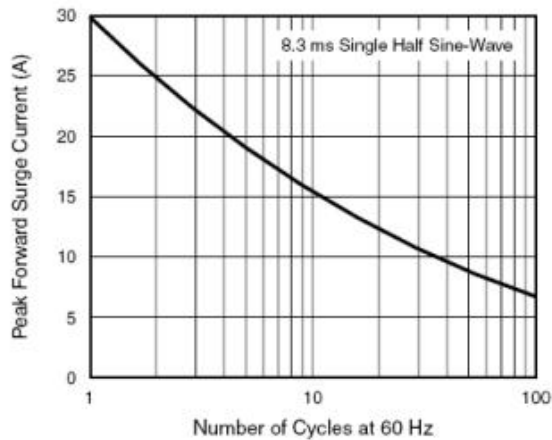


Fig. 2 - Maximum Non-Repetitive Peak Forward Surge Current

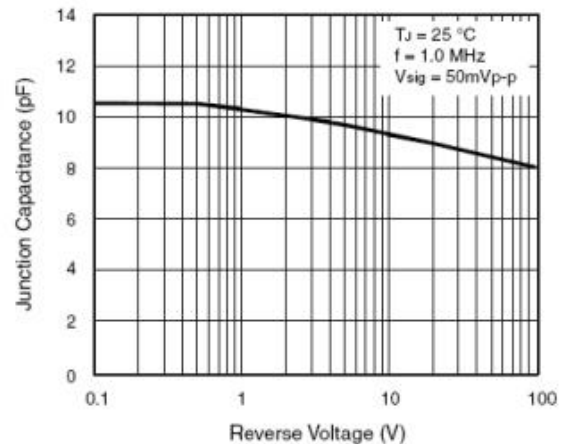


Fig. 5 - Typical Junction Capacitance

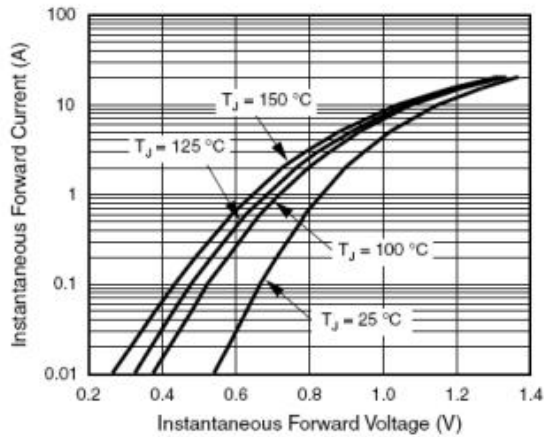


Fig. 3 - Typical Instantaneous Forward Characteristics

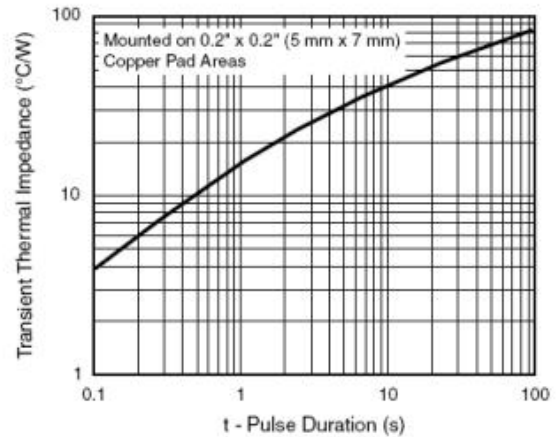
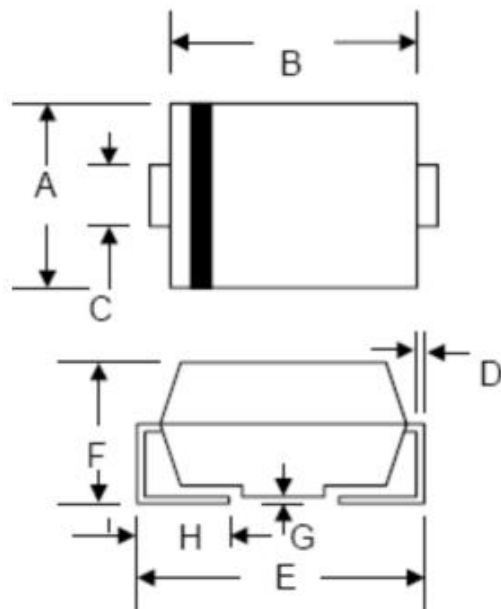


Fig. 6 - Typical Thermal Impedance

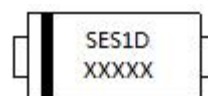
**Mechanical Dimensions SMA**


SYMBOL	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	2.40	2.84	0.094	0.112
B	3.99	4.75	0.157	0.187
C	1.05	1.70	0.041	0.067
D	0.15	0.51	0.006	0.020
E	4.80	5.66	0.189	0.223
F	1.90	2.95	0.075	0.116
G	0.05	0.203	0.002	0.008
H	0.76	1.52	0.030	0.600

**Ordering Information**

Device	Package	Plating	Shipping
SES1D	SMA (Pb-Free)	Pure Sn	5000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

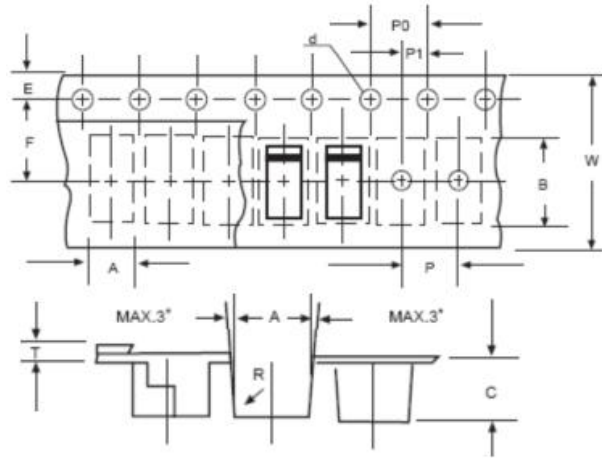
**Marking Diagram**


Where XXXXX is YYWWL

- SES = Device Type
- 1 = Forward Current (1A)
- D = Reverse Voltage (200V)
- YY = Year
- WW = Week
- L = Lot Number

**Cautions:** Molding resin  
Epoxy resin UL:94V-0

**Carrier Tape Specification SMA**



SYMBOL	Millimeters	
	Min.	Max.
A	2.97	3.17
B	5.70	5.90
C	2.32	2.52
d	1.40	1.60
E	1.40	1.60
F	5.60	5.70
P	3.90	4.10
P0	3.90	4.10
P1	1.90	2.10
T	0.25	0.35
W	11.80	12.20

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